

The Silicon TPC System (SITPC)

EUDET Annual meeting 9 October 2007

Jan Timmermans

NIKHEF

1

JRA2 activity/task

- Silicon TPC readout ("SITPC")
 - development MediPix \rightarrow TimePix chip
 - development diagnostic endplate module incl. DAQ
- Purpose: a SiTPC based monitoring system

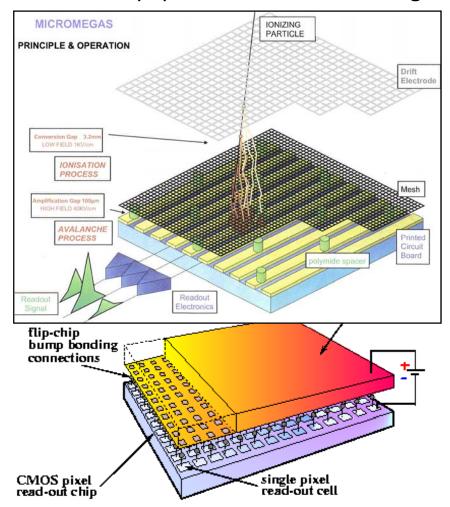
Partners:

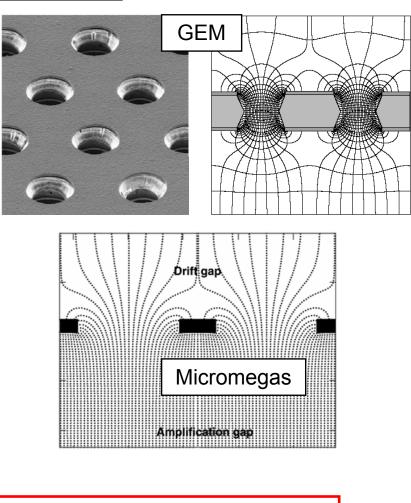
ALU Freiburg, Bonn, CEA Saclay, CERN, NIKHEF Associate: Bucarest SITPC Tasks:

- Develop the Timepix chip that allows to measure the 3rd coordinate (drift time)
- Implementation of Timepix together with GEM and Micromegas into diagnostic endplate system (in progress)
- Performance measurements in test infrastructure at DESY and other places (in progress)
- Develop simulation framework
- Develop DAQ system and integrate in overall DAQ of EUDET infrastructure

Micro Patterned Gaseous Detectors

- High field created by Gas Gain Grids
- Most popular: GEM & Micromegas

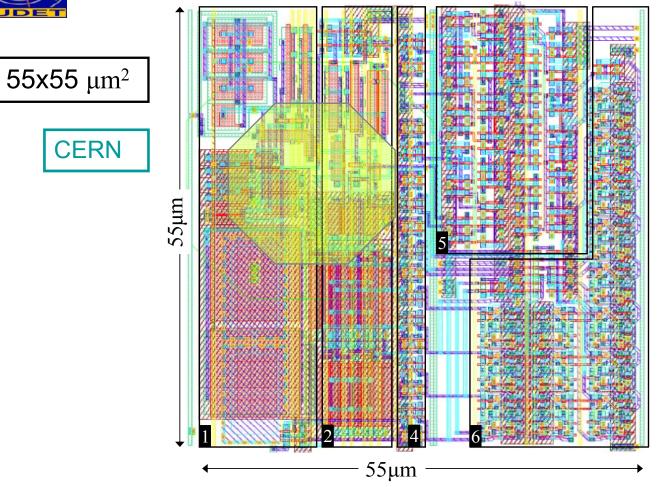








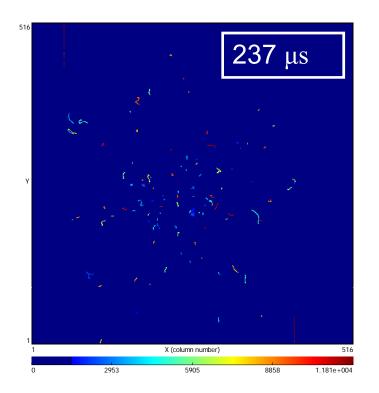
Timepix pixel

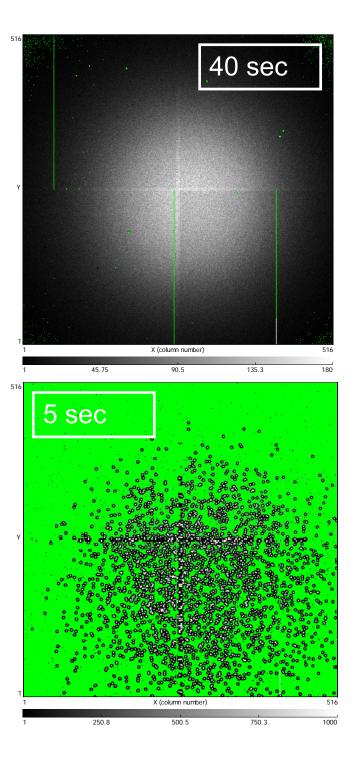


Timepix chip (1st version) produced Sept. 2006 Available for use in detectors since Nov. 2006 CERN (Xavi Llopart/Michael Campbell): first Timepix quad (+ 300 μm Si sensor) •Top-right: Medipix counting mode (⁵⁵Fe)

•Bottom-left: Time mode (⁹⁰Sr)

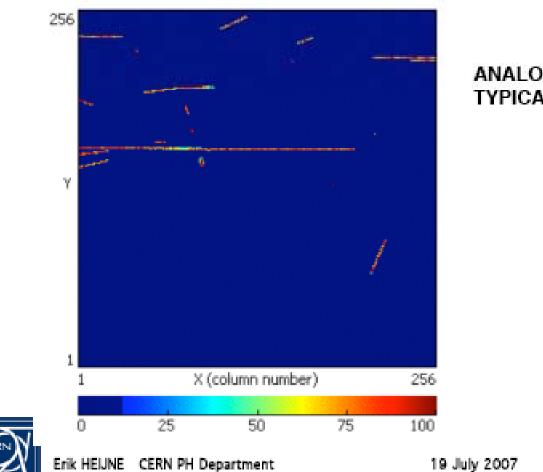
•Bottom-right: time-over-threshold (²⁴¹Am)





Erik Heijne: Timepix (single chip + Si sensor) parallel to beam

H6 120 GeV/c PION BEAM

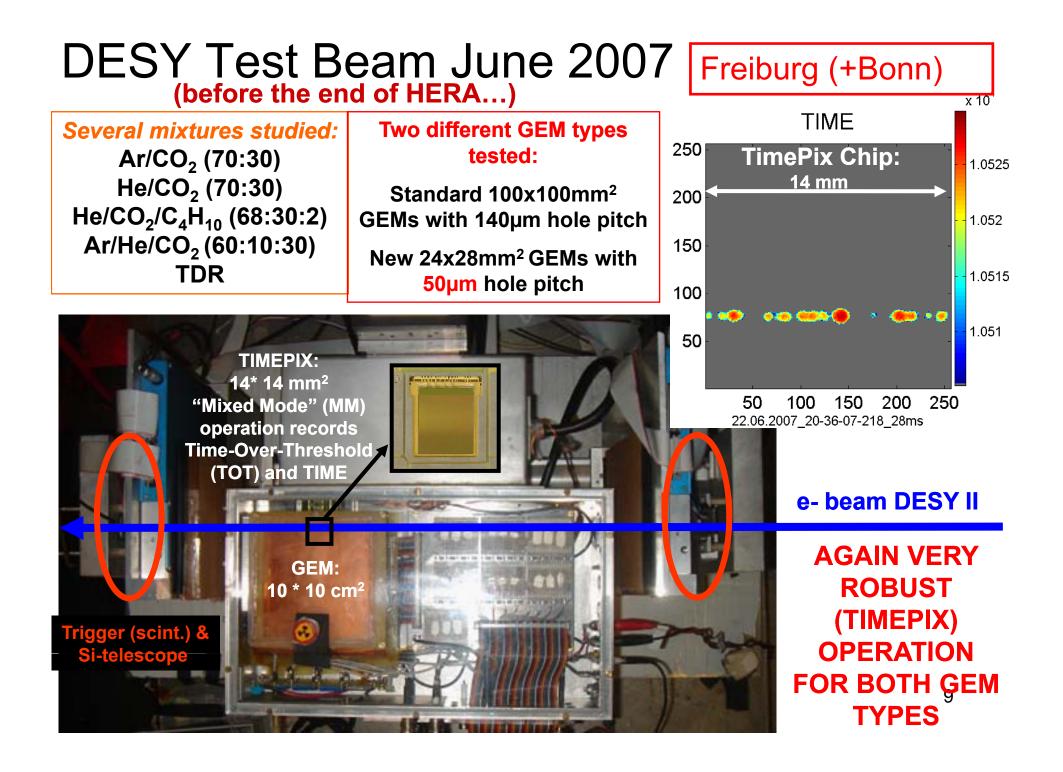


ANALOG MODE TOT TYPICAL SIGNAL ~80 counts



Timepix in gaseous detectors

- With GEM stacks or Micromegas
- Wafer postprocessing:
 - Enlarged pixels
 - Integrated grid
- Discharge protection



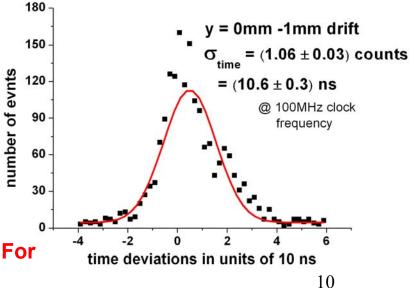
Resolution studies Spatial resolution $\sigma_{max}^2 = \sigma_0^2 + \frac{D_t^2 \cdot y}{1} \cdot D_t$ - transverse diffusion coefficient

Spanal resolution $v_{mean} - v_0 + \frac{1}{n_{el}^{el}}$						
Clustering method		DATA		Simu- lations		
Cluster	Gas	σ_0	D _t ² n ^{el} _{cl}	σ ₀	$\frac{D_t^2}{n_{cl^{el}}}$	
	Ar/CO ₂	21.7 +/-0.5	519 +/-12			
"Island"	He/CO ₂	25.6 +/-1.0	675 +/-16			
	new GEM type Ar/CO ₂	15.4 +/-0.4	405 +/10			
"Saddle Point"	Ar/CO ₂	18.4 +/-2.7	467 +/-36	15.2 +/-3.8	726 +/-41	
	He/CO ₂	27.1 +/-4.9	547 +/-78	19.4 /-4.0	989 +/-54	

- n^{el}-number of primary electrons per clüster
- · y drift length
- $\cdot \sigma_0 \approx 15-25 \mu m$

Time resolution

Time resolution was evaluated in **MM-operation.** A correlation between TOT-maximum and Time was used to correct for time-walk problems (typically 2-3 counts).

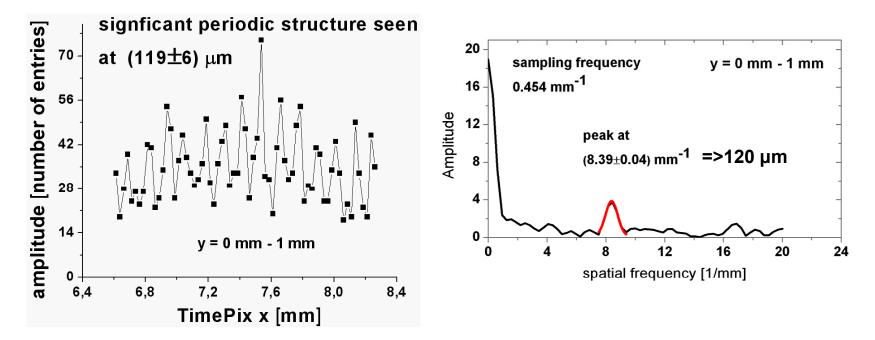


Proves robustness of cluster separation algorithms. For σ_0 good agreement between experiment and simulations. D_t^2/n^{el}_{cl} is in fair agreement.



Substructure due to GEM hole pitch

standard GEM



Is the resolution of a cluster yet affected by the finite pitch of the holes?

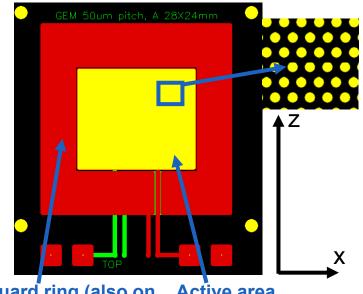
Test runs are taken recently with different orientation with respect to the track and with smaller pitched GEMs (80µm).

Results are expected to be available soon.

New Technical Developments



New GEM type



Guard ring (also on Active area lower side) 28x24mm²

- •Nominal outer hole diameter 30µm in copper
- Inner hole sizes are as small as 17µm-21µm in the Kapton
- •Pitch of holes 50µm
 - •Projected in $x\approx 43 \mu m$

•Projected in $z\approx 25 \mu m$

Post processing on a single chip before after

larger pixels available

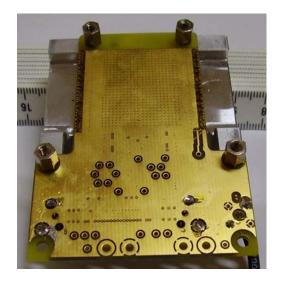
55x55um²

- Idea: collect more charge per larger pixel ⇒ reduction of effective threshold expected
- FMF in Freiburg is going to prepare a TimePix after first tests with MediPix2 12

110x110µm²

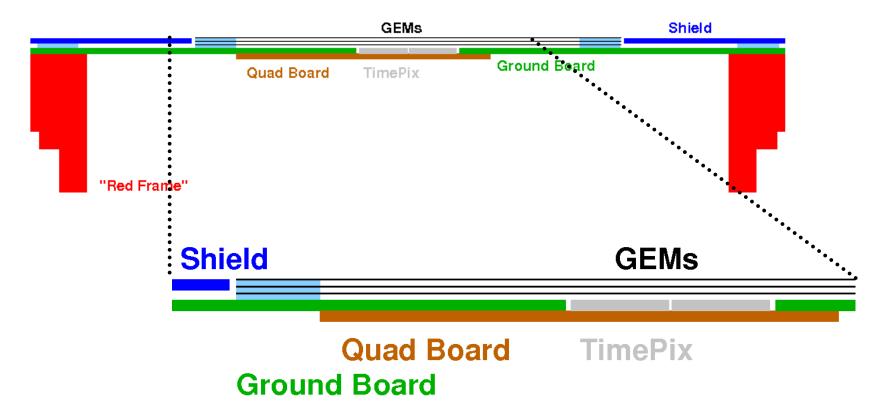
Bonn: TimePix Module for the LP (deliverable by end 2007)

- Based on Medipix2 QuadBoard designed by NIKHEF
- 2x2 TimePix Chips per QuadBoard
- 2 QuadBoards per Module
- QuadBoards glued into PCB back plane



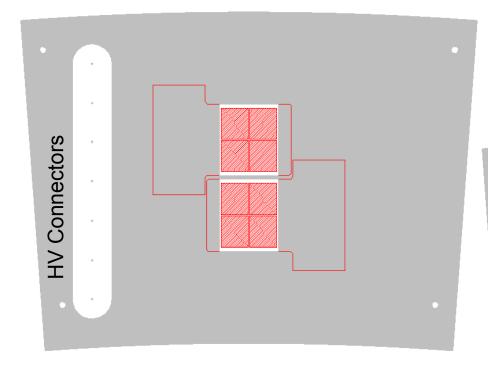


Cross Section

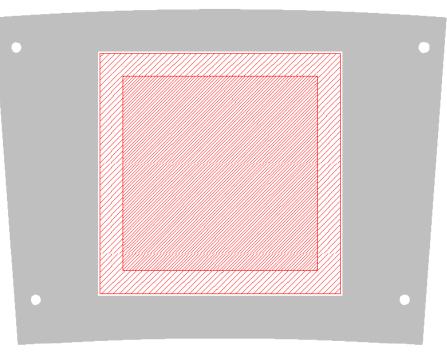


- Three standard CERN GEMs (10x10 mm²)
- Surrounding shield made from a PCB
- 1mm gap between the GEMs
- Total height of active detector: 6mm + connectors

Ground plate with TimePixes

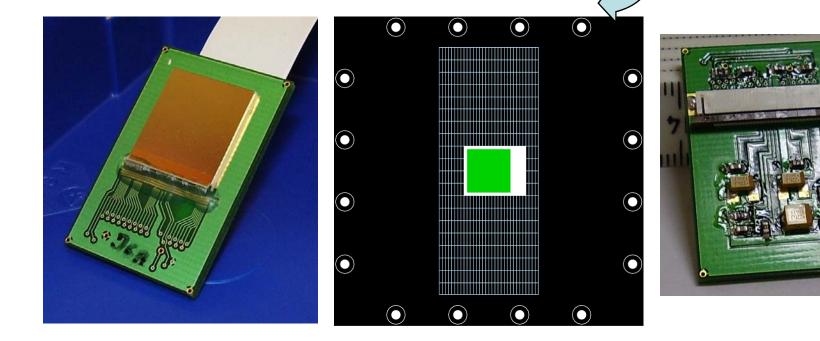


Shield with GEM

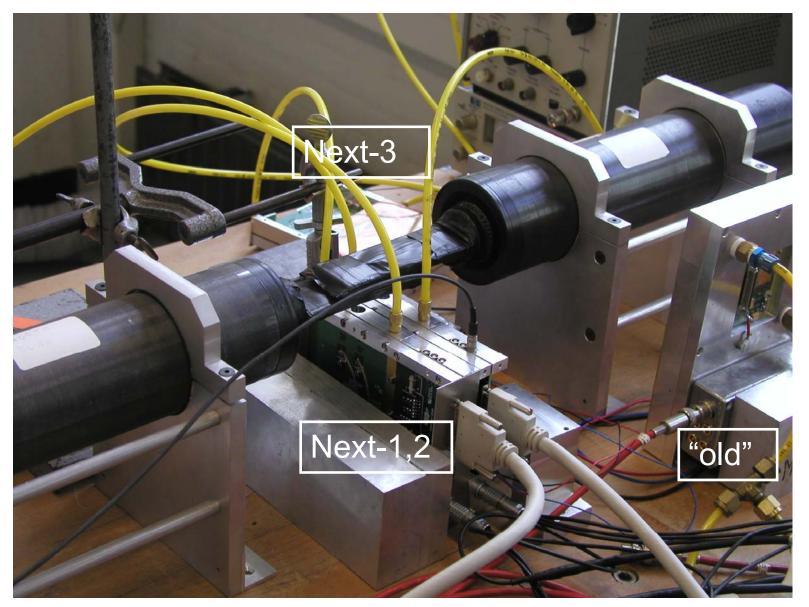


Also: Single Chip Board

- Designed to be as small as possible: Resistors mounted behind the chip
- For use in board together with pads



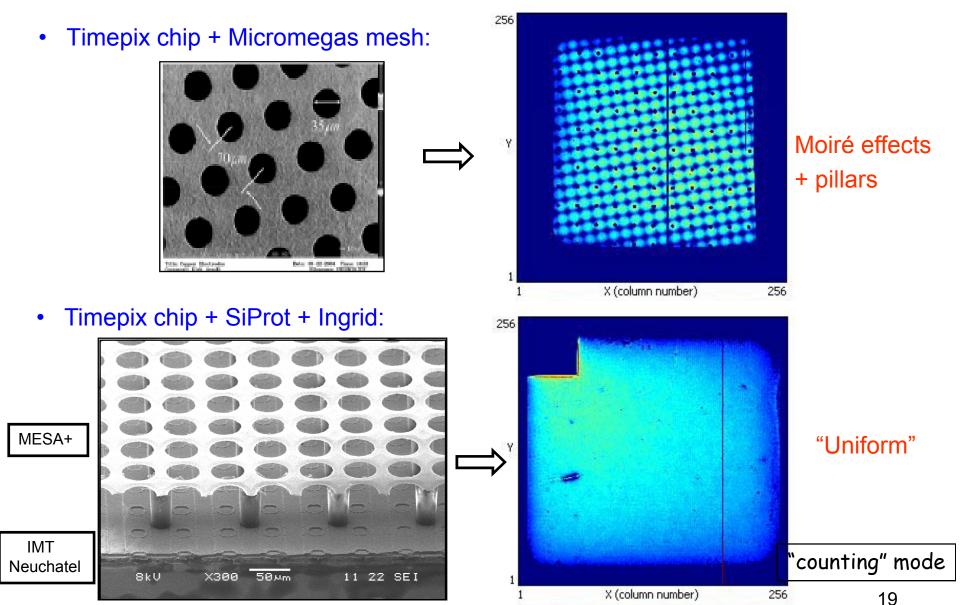
NIKHEF setup (on 24 Aug. 2007)

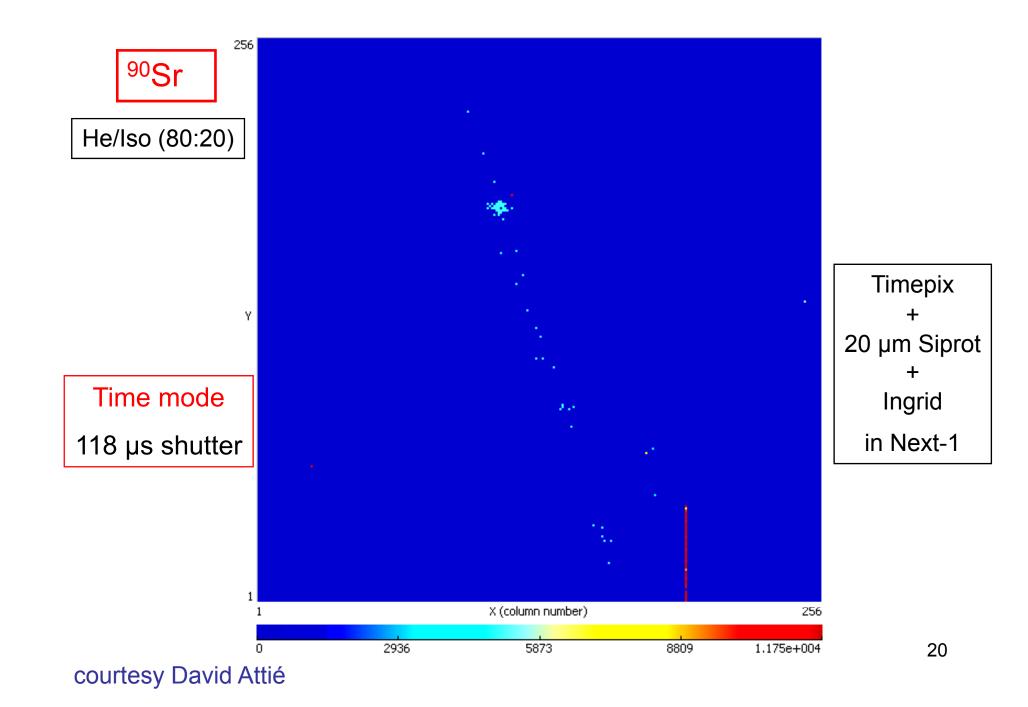


17

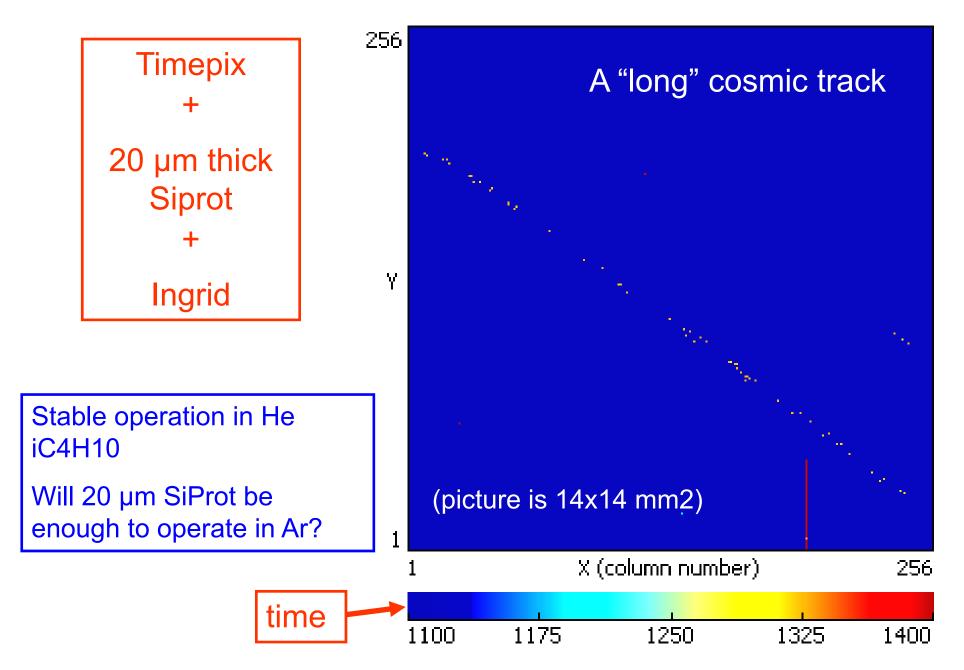
	Status of Timepix usage at NIKHEF
13 dec.	B05 with 3 µm SiProt & Micromegas in He 20% iC4H10 TPX operated 1 month in He
24 jan.	Switch to Ar 20% iC4H10, chip died after 2 days
20 mar.	MediPix2 with 3 µm SiProt & InGrid operated 4 days in He processed MPX
17 apr.	C08 with 3 µm SiProt & Micromegas & guard electrode (G.E.) in He Operated 3
25 jul.	Stop C08 after 3 months of continuous operation in He He iC4H10
	E09 with 20 µm SiProt & InGrid placed
22 aug.	A06 with 20 μm SiProt & Micromegas placed in NEXT-2 chamber in He
04 sep. 23 sep.	Flush NEXT-2 (A06) with Ar, stable operation for >20 days! Flush NEXT-1 (E09) with Ar, same nice results Operated in Ar iC4H10
26 sep.	Introduce Thorium in NEXT-2 (A06), provoke discharges Recording alpha's tracks & even more 18

Full post-processing of a TimePix

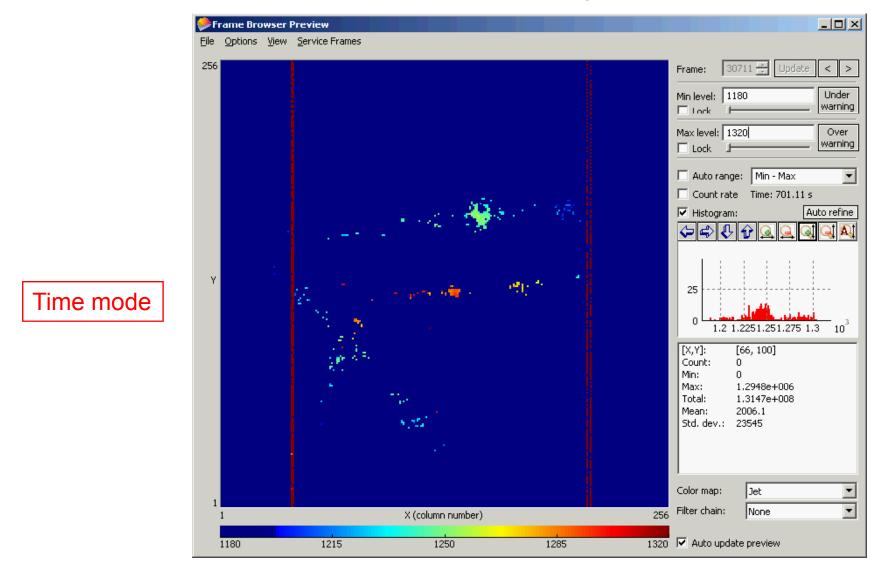




The "typical" track



Stable operation in Argon too!

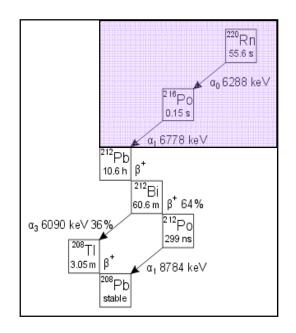


After 2 weeks of cosmic event recording, it was time for a definitive assessment whether 20 μ m SiProt is enough to protect against discharges...

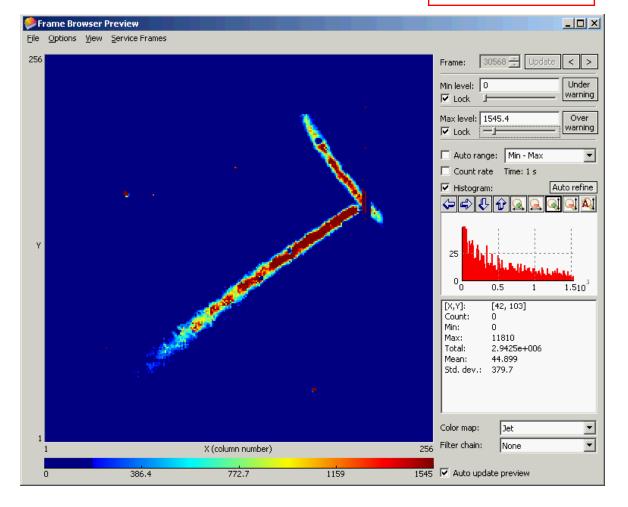
Final assessment: spark-proofness

- Provoke discharges by introducing small amount of Thorium in the Ar gas
 - Thorium decays to Radon 222 which emits 2 alphas of 6.3 & 6.8 MeV
 - Depose on average $2.5.10^5 \& 2.7.10^5 e$ in Ar/iC₄H₁₀ 80/20 at -420 V on the grid, likely to trigger discharges

Charge mode



Since 1 week, some 5.10⁴ alpha events recorded in 1% of which ...



... discharges are observed !

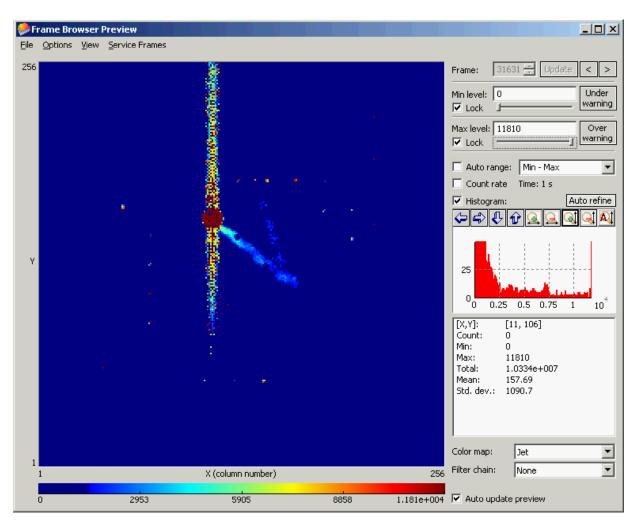
For the 1st time: image of discharges are being recorded

Round-shaped pattern of some 100 overflow pixels

Perturbations in the concerned column pixels

- Threshold?
- Power?

Chip keeps working !!





TimePix wafer tests at CERN (together with Freiburg, NIKHEF)

Class					TimePi	x classi	fication			To	tal
A No dead columns	Wafer n°	Location	Α	В	С	D	E	F	Fnt	Wafer	A+B
B 1 dead column	8_A9FWR6X	CERN	31	27	6	11	12	20	0	107	58
C 2 dead columns	9_ACFWR3X	CERN	42	15	13	10	9	17	1	107	57
D >2 dead columns	10_A6FWQ5X	CERN	40	27	7	12	11	9	1	107	67
E Bad DACs	11_ATFWTLX	CERN	54	18	7	6	14	8	0	107	72
F Bad Digital Test	12_ASFWTMX	CERN	45	21	7	2	18	13	1	107	66
Fnt Not tested	13_ARFWTNX	CERN	15	18	14	27	17	16	0	107	33
	14_A5FWQTX	Diced	44	26	3	6	8	20	0	107	70
	15_AQFWTPX	VTT	55	20	10	6	9	7	0	107	75
	16_GX11ILX	CERN	44	27	8	10	13	5	0	107	71
	17_G111GIX	CERN	41	31	8	7	14	6	0	107	72
	18_GG11G3X	CERN	58	26	5	4	9	5	0	107	84
20 wafers from the	19_GF11G4X	CERN	49	30	9	6	9	4	0	107	79
first run tested	20_GV11INX	CERN	51	23	15	13	3	2	0	107	74
	21_GV11GPX	CERN	49	27	8	9	9	5	0	107	76
\rightarrow ~ 66 % of chips are	22_GZ11H2X	CERN	48	25	9	7	14	4	0	107	73
usable	23_GU11H7X	CERN	58	26	2	3	12	6	0	107	84
usuble	24_GY11lKX	CERN	47	23	8	6	18	5	0	107	70
	25_GW11H5X	CERN	46	18	8	15	2	18	0	107	64
72.9% yield	26_GS11H9X	CERN	35	39	7	8	11	7	0	107	74
	27_GH11G2X	CERN	56	27	5	4	13	2	0	107	83
-											
	TOTAL		908	494	159	172	225	179	3	2140	1402
(A+B+C)	(%)		42,4	23,1	7,4	8,0	10,5	8,4	0,1	100	65,5

dapnia

CEC) saclay



TimePix/Micromegas chamber at Saclay



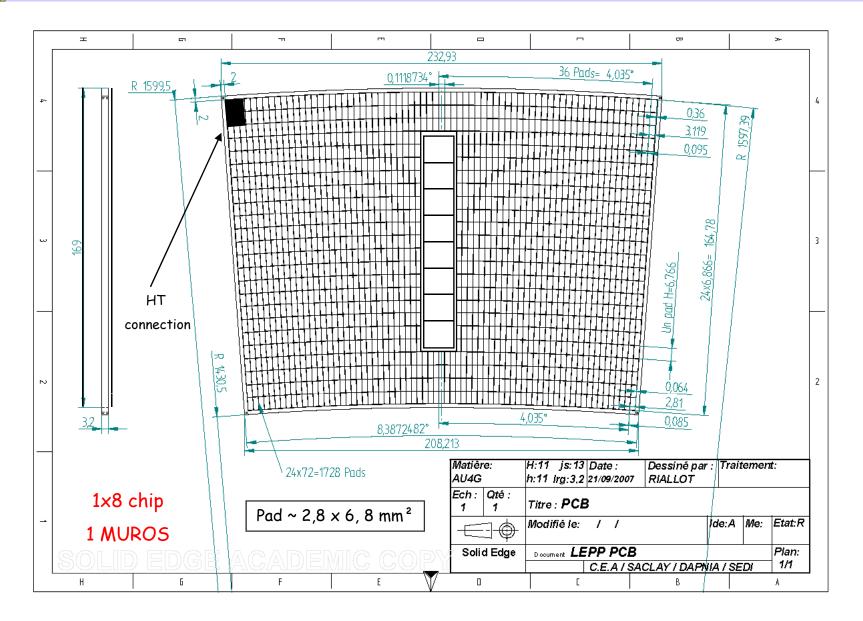


- The field cage is ready to work in He/Iso 80/20 (6 kV on the cathode)
- 1 TimePix dead by HV accident
- 2 TimePix Chip don't show the same behavior after putting up the micromegas mesh
- Several chips with Siprot now available

 $\hat{\mathbf{A}}$



Deliverable endplate with TimePix

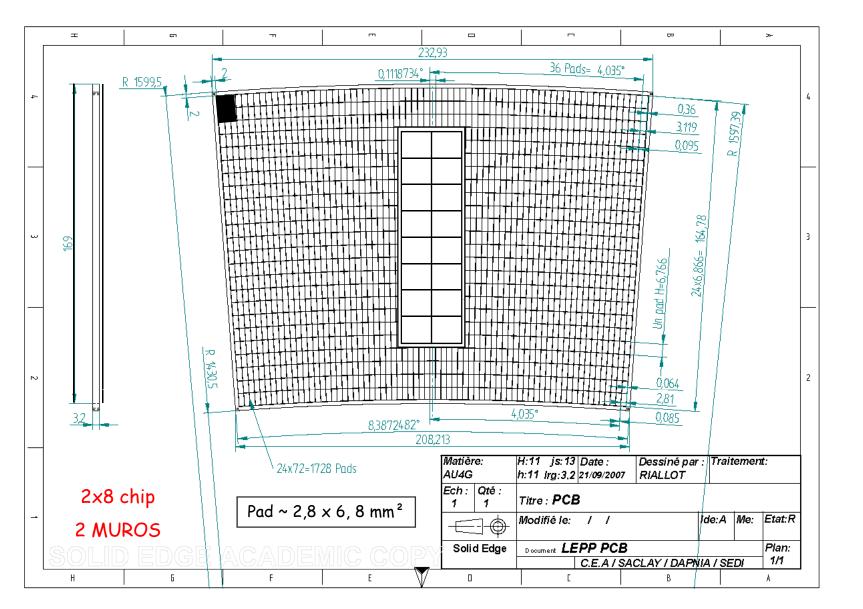


dapnia

CEO saclay



Large Prototype Endplate



dapnia

CEO saclay

Summary

- A lot of progress made in last year; not mentioned many details on track resolution studies, reconstruction software development, signal development
- Part of the technology is ready
- Discharge protection seems working

Next:

- Build larger detector systems with fast readout; first step ("deliverable") endplate structure end of 2007 (few 1-2 months later)
- Further beam tests (and in B field)
- Assess track and dE/dx resolutions

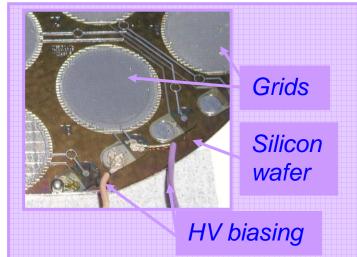
Backup slides

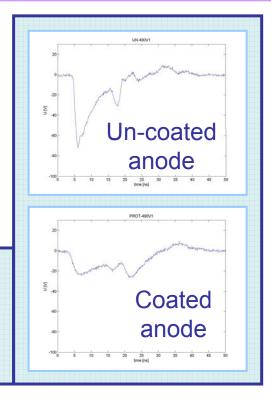
Wafer post-processing(s)

- Idea: use micro-electronic techniques to optimize CMOS pixel chip performances
 - Gas amplification structures
 - Current limiting coatings

InGrid: a Grid integrated on Si

- Maximize detection efficiency
 - alignment holes/pads
- Minimize dead areas
 - small pillars Ø, full pixel area coverage
- SiProt: a low T deposited aSi:H layer
 - Up to 30 μm thick films, ~10^{11} $\Omega.cm$
 - Attenuate discharge current

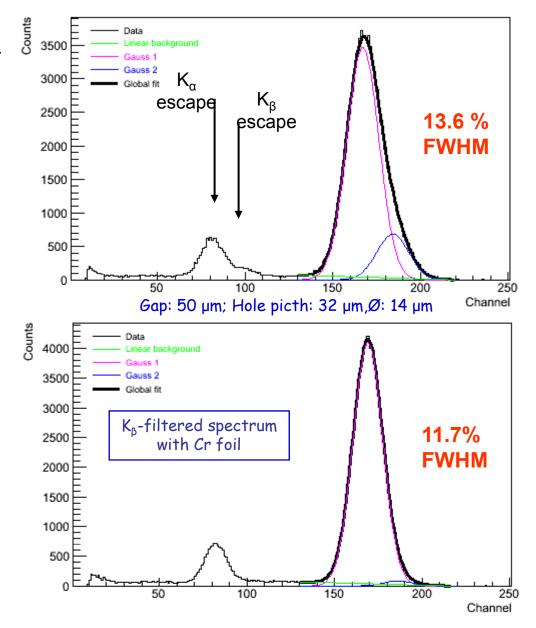




New Ingrid developments and results

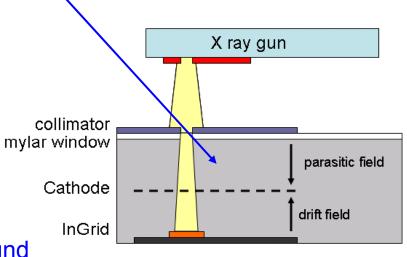
- Process improvement: grids much flatter
 - Extremely good energy resolution: 13.6 % FWHM with ⁵⁵Fe in P10
 - Removal of K_{β} 6.5 keV line: 11.7 % @ 5.9 keV in P10
- New wafer masks: hole pitches down to 20 µm with various diameters and gaps
 - Investigate Micromegas geometry
 - Test of the ion backflow theory
- Until now: 1 µm thin Al but can now be increased to 5 µm by electrolysis

Expect less damaged from sparks



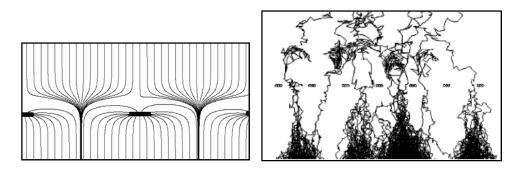
InGrid ion backflow measurements (I)

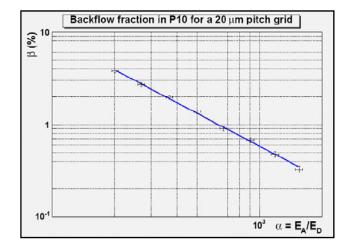
- Measurements started in Saclay with D. Attié & P. Colas
- Main issues encountered:
 - Gas gap between detector window & cathode
 - "Parasitic" field
 Unwanted contribution to primary current
 - Small grid area
 - high X flux for significant primary current (recombination problem @ low drift field)
 - bad collection of "long" range photoe-
- Solutions:
 - Operate the detector with cathode at ground
 - Reduce X-ray energy (~ 9 keV) and flux
- Now:
 - measurements of the primary and backflow currents accurate to the pA!
 - Good measurements up to field ratio of 1000: backflow fraction of few 10⁻³ in P10 gas.

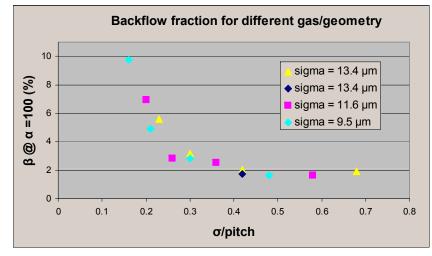


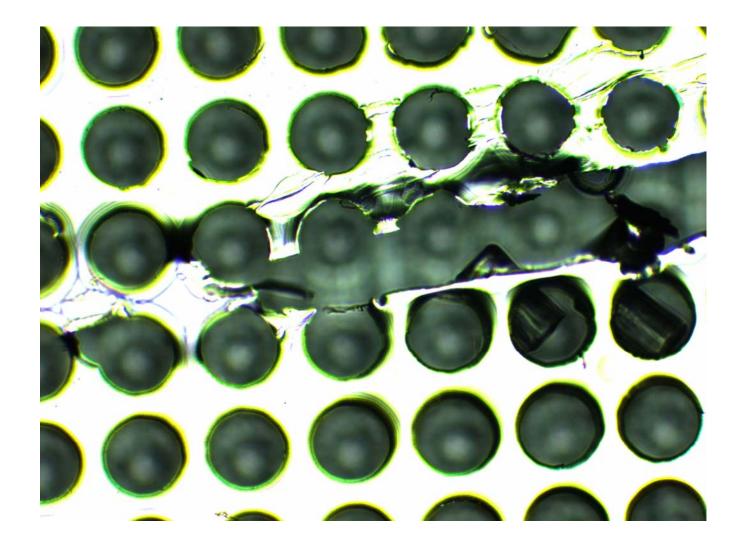
InGrid ion backflow measurements (II)

- Phenomenon depends on:
 - Avalanche charge distribution
 - Funnel size
- therefore on the gas and grid geometry
 - Q density in the funnel decreases with the avalanche transverse diffusion
 - Funnel size decreases with the field ratio and hole pitch
- Backflow fraction reaches a (minimum) plateau
 - Occurs when ions backflow through neighboring holes
 - Simulation predicts this to occur at $\sigma/p = 0.5$







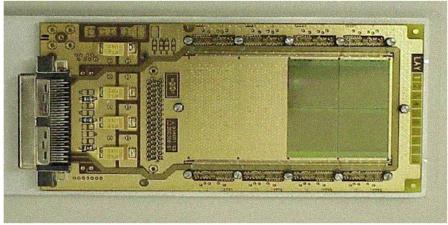


A "scratch" occurred during production Ingrid; Loose parts removed. Ingrid working!

Further Developments

RELAXD project (Dutch/Belgian) NIKHEF,Panalytical,IMEC,Canberra:

- Chip tiling: large(r) detector surfaces (2x2, 2x4 chips)
- Through Si connectivity: avoiding bonding wires
- Fast readout technology (~5 Gb/s)



Somewhat slower progress than expected:

Still hope for "through Si vias" (with Medipix chips) later this year!

summary timetable

- ✓ 1st version Timepix operational: 1/2007 9/2006
 ✓ First m.i.p. signals with Timepix: ~4/2007 11/2006
- Gain experience with Timepix during 2007
- Development 2nd iteration Timepix during 2007

 \rightarrow 3/2008

- Endplate infrastructure: 1/2008
- Full SITPC infrastructure incl. DAQ available:

1/2009

TimePix Reconstruction



Data Structure	Processor Name	Collection Name
TrackerRawData		TimePixRawData
٦	TimePixZeroSuppressionProcessor	
TrackerRawData	7	FimePixZeroSuppressedRawData
	TimePixClusterFinderProcessor	
TrackerHit		TimePixHitCandidates
Time	PixClusterProjectionSeparatorProce	ssor
TrackerHit		TimePixSepHitCandidates
Ti	mePixHitCenterCalculatorProcessor	
TrackerHit		TimePixHits

